TEXAS INSTRUMENTS

SN54HC595, SN74HC595

SCLS041I – DECEMBER 1982 – REVISED SEPTEMBER 2015

SNx4HC595 8-Bit Shift Registers With 3-State Output Registers

1 Features

- 8-Bit Serial-In, Parallel-Out Shift
- Wide Operating Voltage Range of 2 V to 6 V
- High-Current 3-State Outputs Can Drive Up to 15 LSTTL Loads
- Low Power Consumption: 80-μA (Maximum) I_{CC}
- t_{pd} = 13 ns (Typical)
- ±6-mA Output Drive at 5 V
- Low Input Current: 1 μA (Maximum)
- Shift Register Has Direct Clear
- On Products Compliant to MIL-PRF-38535, All Parameters Are Tested Unless Otherwise Noted. On All Other Products, Production Processing Does Not Necessarily Include Testing of All Parameters.

2 Applications

- Network Switches
- Power Infrastructure
- LED Displays
- Servers

3 Description

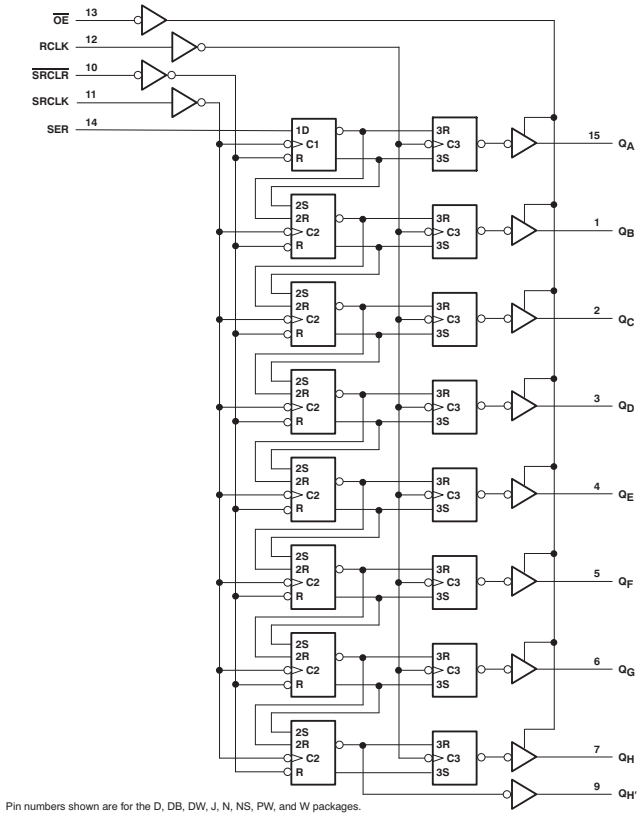
The SNx4HC595 devices contain an 8-bit, serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. The storage register has parallel 3-state outputs. Separate clocks are provided for both the shift and storage register. The shift register has a direct overriding clear (SRCLR) input, serial (SER) input, and serial outputs for cascading. When the output-enable ($\overline{OE}$) input is high, the outputs are in the high-impedance state.

Device Information[1]

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN54HC595	LCCC (20)	8.89 mm x 8.89 mm
	CDIP (16)	21.34 mm x 6.92 mm
SN74HC595	PDIP (16)	19.31 mm × 6.35 mm
	SOIC (16)	9.90 mm x 3.90 mm
	SOIC (16)	10.30 mm x 7.50 mm
	SSOP (16)	6.20 mm x 5.30 mm
	TSSOP (16)	5.00 mm x 4.40 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)



Pin numbers shown are for the D, DB, DW, J, N, NS, PW, and W packages.

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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

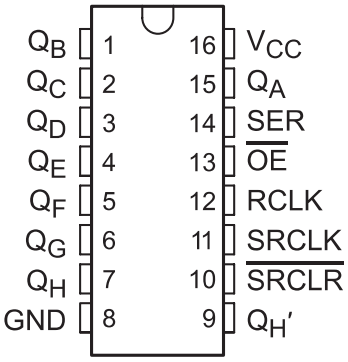
Changes from Revision H (November 2009) to Revision I	Page
• Added *Applications* section, *Device Information* table, *Pin Configuration and Functions* section, *ESD Ratings* table, *Thermal Information* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section	1
• Deleted *Ordering Information* table.	1
• Added Military Disclaimer to *Features* list.	1

5 Device Comparison Table

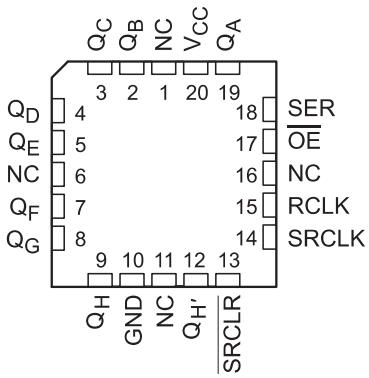
PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN54HC595FK	LCCC (20)	8.89 mm x 8.89 mm
SN54HC595J	CDIP (16)	21.34 mm x 6.92 mm
SN74HC595N	PDIP (16)	19.31 mm × 6.35 mm
SN74HC595D	SOIC (16)	9.90 mm x 3.90 mm
SN74HC595DW	SOIC (16)	10.30 mm x 7.50 mm
SN74HC595DB	SSOP (16)	6.20 mm x 5.30 mm
SN74HC595PW	TSSOP (16)	5.00 mm x 4.40 mm

6 Pin Configuration and Functions

D, N, NS, J, DB, or PW Package
16-Pin SOIC, PDIP, SO, CDIP, SSOP, or TSSOP
Top View



FK Package
20-Pin LCCC
Top View



Pin Functions

PIN			I/O	DESCRIPTION
NAME	SOIC, PDIP, SO, CDIP, SSOP, or TSSOP	LCCC		
GND	8	10	—	Ground Pin
$\overline{OE}$	13	17	I	Output Enable
Q_A	15	19	O	Q_A Output
Q_B	1	2	O	Q_B Output
Q_C	2	3	O	Q_C Output
Q_D	3	4	O	Q_D Output
Q_E	4	5	O	Q_E Output
Q_F	5	7	O	Q_F Output
Q_G	6	8	O	Q_G Output
Q_H	7	9	O	Q_H Output
$Q_{H'}$	9	12	O	$Q_{H'}$ Output
RCLK	12	14	I	RCLK Input
SER	14	18	I	SER Input
SRCLK	11	14	I	SRCLK Input
$\overline{SRCLR}$	10	13	I	$\overline{SRCLR}$ Input
NC	—	1	—	No Connection
		16		
		11		
		16		
V_{CC}	—	20	—	Power Pin

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	7	V
I_{IK}	Input clamp current(2)	$V_I < 0$ or $V_I > V_{CC}$		±20	mA
I_{OK}	Output clamp current (2)	$V_O < 0$ or $V_O > V_{CC}$		±20	mA
I_O	Continuous output current	$V_O = 0$ to V_{CC}		±35	mA
	Continuous current through V_{CC} or GND			±70	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			SN54HC595			SN74HC595			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage		2	5	6	2	5	6	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5			1.5			V
		V_{CC} = 4.5 V	3.15			3.15			
		V_{CC} = 6 V	4.2			4.2			
V_{IL}	Low-level input voltage	V_{CC} = 2 V			0.5			0.5	V
		V_{CC} = 4.5 V			1.35			1.35	
		V_{CC} = 6 V			1.8			1.8	
V_I	Input voltage		0		V_{CC}	0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	0		V_{CC}	V
$\Delta t/\Delta v$	Input transition rise or fall time(2)	V_{CC} = 2 V			1000			1000	ns
		V_{CC} = 4.5 V			500			500	
		V_{CC} = 6 V			400			400	
T_A	Operating free-air temperature		–55		125	–40		85	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.
(2) If this device is used in the threshold region (from V_{IL}max = 0.5 V to V_{IH} min = 1.5 V), there is a potential to go into the wrong state from induced grounding, causing double clocking. Operating with the inputs at t_t = 1000 ns and V_{CC} = 2 V does not damage the device; however, functionally, the CLK inputs are not ensured while in the shift, count, or toggle operating modes.

7.4 Thermal Information

THERMAL METRIC(1)		SN74AHCT595						UNIT
		D (SOIC)	DB (SSOP)	DW (SOIC)	N (PDIP)	NS (SO)	PW (TSSOP)	
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	73	82	57	67	64	108	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

7.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

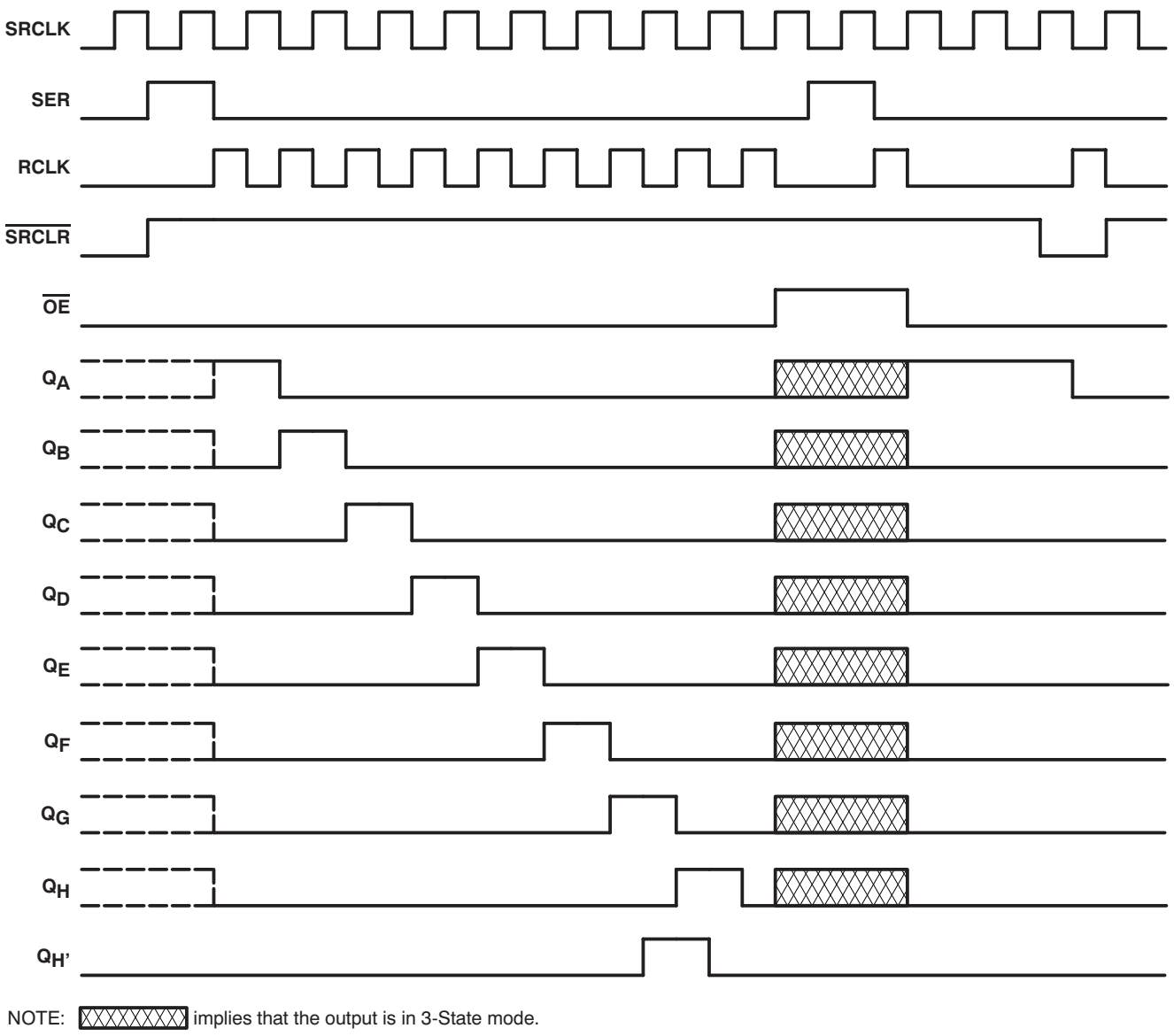
PARAMETER	TEST CONDITIONS		V_{CC}	T_A = 25°C			SN54HC595		SN74HC595		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}	$V_I = V_{IH}$ or V_{IL}	I_{OH} = –20 µA	2 V	1.9	1.998		1.9		1.9		V
			4.5 V	4.4	4.499		4.4		4.4		
			6 V	5.9	5.999		5.9		5.9		
		$Q_{H'}$, I_{OH} = –4 mA	4.5 V	3.98	4.3		3.7		3.84		
		Q_A – Q_H, I_{OH} = –6 mA		3.98	4.3		3.7		3.84		
		$Q_{H'}$, I_{OH} = −5.2 mA	6 V	5.48	5.8		5.2		5.34		
		Q_A – Q_H, I_{OH} = –7.8 mA		5.48	5.8		5.2		5.34		
V_{OL}	$V_I = V_{IH}$ or V_{IL}	I_{OL} = 20 µA	2 V		0.002	0.1		0.1		0.1	V
			4.5 V		0.001	0.1		0.1		0.1	
			6 V		0.001	0.1		0.1		0.1	
		$Q_{H'}$, I_{OL} = 4 mA	4.5 V		0.17	0.26		0.4		0.33	
		Q_A – Q_H, I_{OL} = 6 mA			0.17	0.26		0.4		0.33	
		$Q_{H'}$, I_{OL} = 5.2 mA	6 V		0.15	0.26		0.4		0.33	
		Q_A – Q_H, I_{OL} = 7.8 mA			0.15	0.26		0.4		0.33	
I_I	$V_I = V_{CC}$ or 0		6 V		±0.1	±100		±1000		±1000	nA
I_{OZ}	$V_O = V_{CC}$ or 0, Q_A – Q_H		6 V		±0.01	±0.5		±10		±5	µA
I_{CC}	$V_I = V_{CC}$ or 0, I_O = 0		6 V			8		160		80	µA
C_i			2 V to 6 V		3	10		10		10	pF

7.6 Timing Requirements

over operating free-air temperature range (unless otherwise noted)

			V_{CC}	T_A = 25°C		SN54HC595		SN74HC595		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		2 V		6		4.2		5	MHz
			4.5 V		31		21		25	
			6 V		36		25		29	
t_w	Pulse duration	SRCLK or RCLK high or low	2 V	80		120		100		ns
			4.5 V	16		24		20		
			6 V	14		20		17		
		$\overline{SRCLR}$ low	2 V	80		120		100		
			4.5 V	16		24		20		
			6 V	14		20		17		
t_{su}	Set-up time	SER before SRCLK↑	2 V	100		150		125		ns
			4.5 V	20		30		25		
			6 V	17		25		21		
		SRCLK↑ before RCLK↑(1)	2 V	75		113		94		
			4.5 V	15		23		19		
			6 V	13		19		16		
		$\overline{SRCLR}$ low before RCLK↑	2 V	50		75		65		
			4.5 V	10		15		13		
			6 V	9		13		11		
		$\overline{SRCLR}$ high (inactive) before SRCLK↑	2 V	50		75		60		
			4.5 V	10		15		12		
			6 V	9		13		11		
t_h	Hold time, SER after SRCLK↑		2 V	0		0		0		ns
			4.5 V	0		0		0		
			6 V	0		0		0		

(1) This set-up time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.



NOTE: ▨ implies that the output is in 3-State mode.

Figure 1. Timing Diagram

7.7 Switching Characteristics

Over recommended operating free-air temperature range.

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V_{CC}	T_A = 25°C			SN54HC595		SN74HC595		UNIT
					MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f_{max}			50 pF	2 V	6	26		4.2		5		MHz
				4.5 V	31	38		21		25		
				6 V	36	42		25		29		
t_{pd}	SRCLK	$Q_{H'}$	50 pF	2 V		50	160		240		200	ns
				4.5 V		17	32		48		40	
				6 V		14	27		41		34	
	RCLK	Q_A – Q_H	50 pF	2 V		50	150		225		187	
				4.5 V		17	30		45		37	
				6 V		14	26		38		32	
t_{PHL}	$\overline{SRCLR}$	$Q_{H'}$	50 pF	2 V		51	175		261		219	ns
				4.5 V		18	35		52		44	
				6 V		15	30		44		37	
t_{en}	$\overline{OE}$	Q_A – Q_H	50 pF	2 V		40	150		255		187	ns
				4.5 V		15	30		45		37	
				6 V		13	26		38		32	
t_{dis}	$\overline{OE}$	Q_A – Q_H	50 pF	2 V		42	200		300		250	ns
				4.5 V		23	40		60		50	
				6 V		20	34		51		43	
t_t		Q_A – Q_H	50 pF	2 V		28	60		90		75	ns
				4.5 V		8	12		18		15	
				6 V		6	10		15		13	
		$Q_{H'}$	50 pF	2 V		28	75		110		95	
				4.5 V		8	15		22		19	
				6 V		6	13		19		16	
t_{pd}	RCLK	Q_A – Q_H	150 pf	2 V		60	200		300		250	ns
				4.5 V		22	40		60		50	
				6 V		19	34		51		43	
t_{en}	$\overline{OE}$	Q_A – Q_H	150 pf	2 V		70	200		298		250	ns
				4.5 V		23	40		60		50	
				6 V		19	34		51		43	
t_t		Q_A – Q_H	150 pf	2 V		45	210		315		265	ns
				4.5 V		17	42		63		53	
				6 V		13	36		53		45	

7.8 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	No load	400	pF

7.9 Typical Characteristics

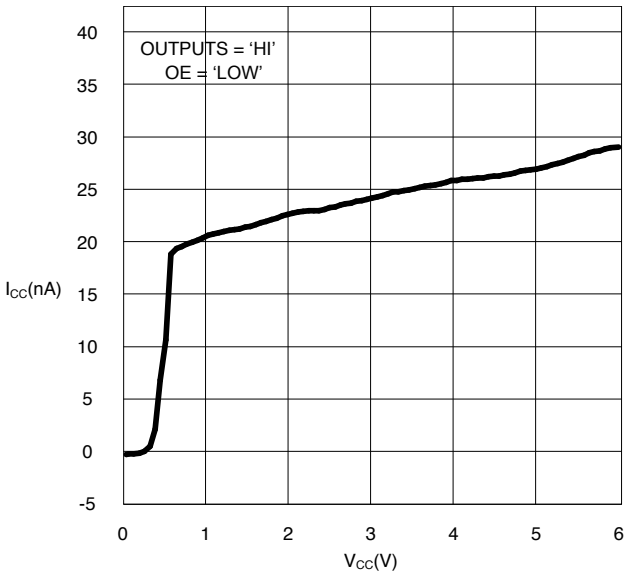
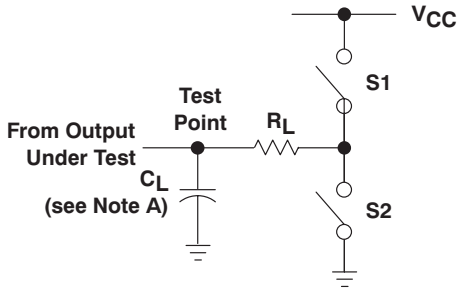


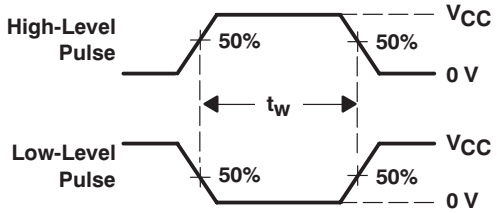
Figure 2. SN74HC595 I_{CC} vs. V_{CC}

8 Parameter Measurement Information

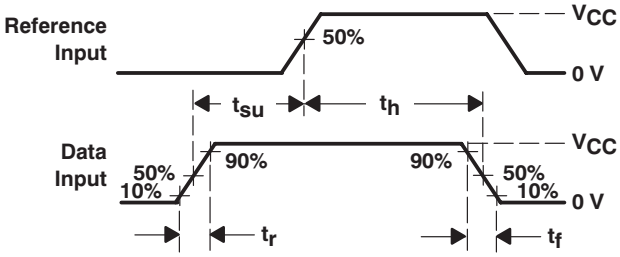


LOAD CIRCUIT

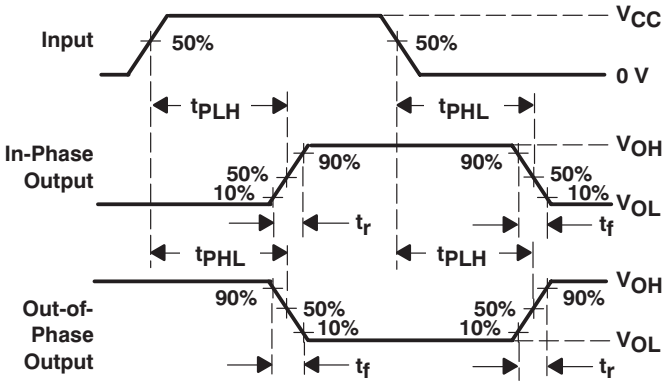
PARAMETER		R_L	C_L	S1	S2
t_{en}	t_{PZH}	1 kΩ	50 pF or 150 pF	Open	Closed
	t_{PZL}			Closed	Open
t_{dis}	t_{PHZ}	1 kΩ	50 pF	Open	Closed
	t_{PLZ}			Closed	Open
t_{pd} or t_t			50 pF or 150 pF	Open	Open



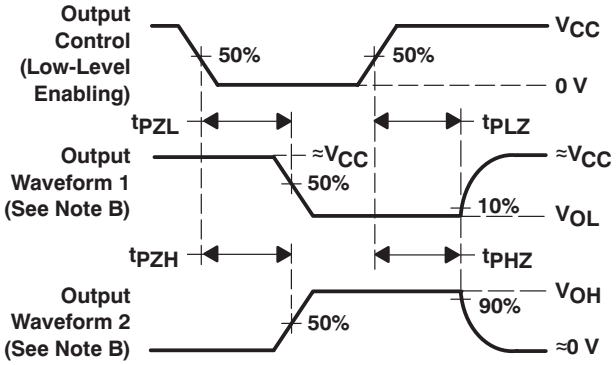
VOLTAGE WAVEFORMS
PULSE DURATIONS



VOLTAGE WAVEFORMS
SETUP AND HOLD AND INPUT RISE AND FALL TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY AND OUTPUT TRANSITION TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES FOR 3-STATE OUTPUTS

NOTES: A. C_L includes probe and test-fixture capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r = 6 ns, t_f = 6 ns.
D. For clock inputs, f_{max} is measured when the input duty cycle is 50%.
E. The outputs are measured one at a time, with one input transition per measurement.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PZL} and t_{PZH} are the same as t_{en}.
H. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 3. Load Circuit and Voltage Waveforms

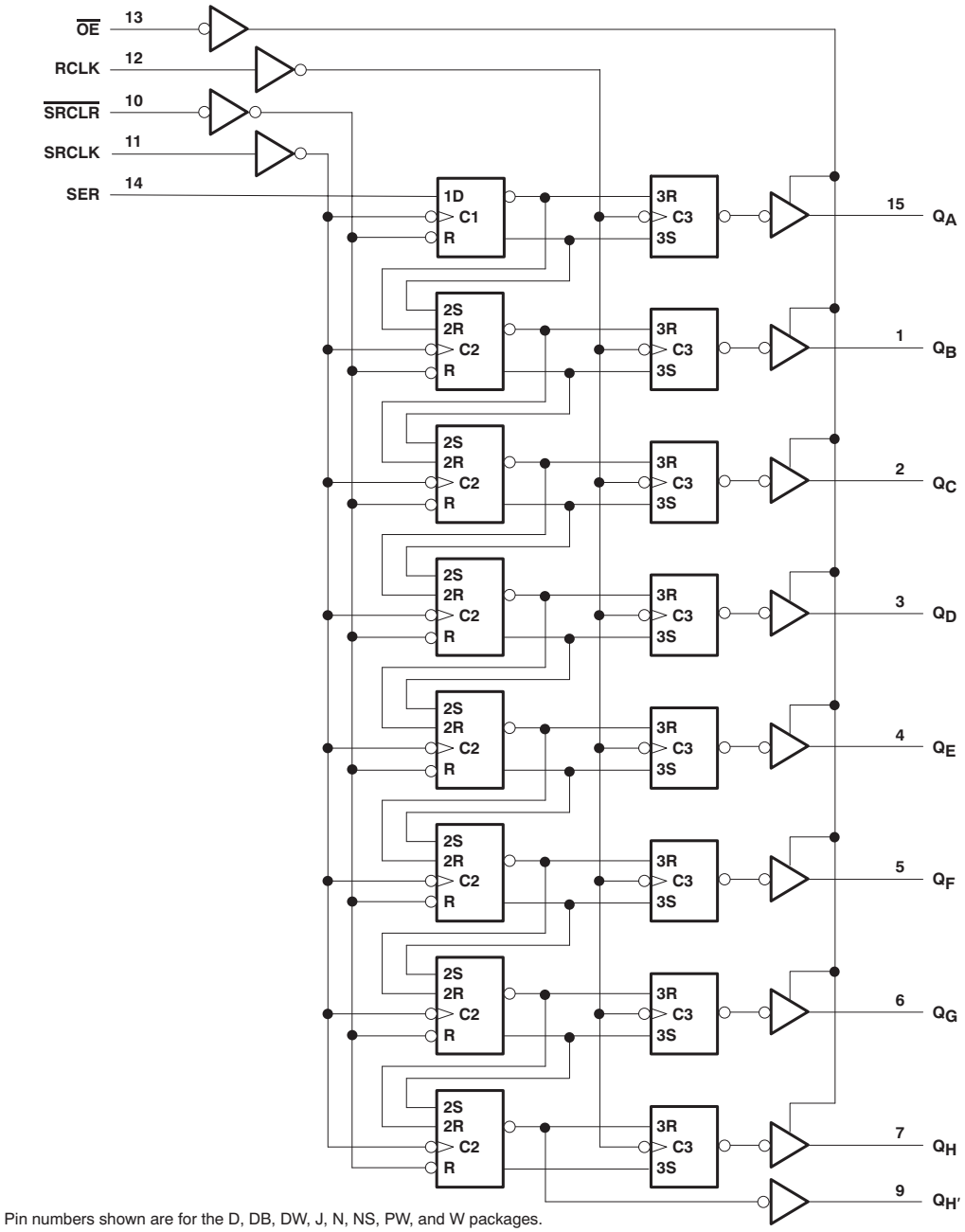
9 Detailed Description

9.1 Overview

The SNx4HC595 is part of the HC family of logic devices intended for CMOS applications. The SNx4HC595 is an 8-bit shift register that feeds an 8-bit D-type storage register.

Both the shift register clock (SRCLK) and storage register clock (RCLK) are positive-edge triggered. If both clocks are connected together, the shift register always is one clock pulse ahead of the storage register.

9.2 Functional Block Diagram



Pin numbers shown are for the D, DB, DW, J, N, NS, PW, and W packages.

Figure 4. Logic Diagram (Positive Logic)

9.3 Feature Description

The SNx4HC595 devices are 8-bit Serial-In, Parallel-Out Shift Registers. They have a wide operating current of 2 V to 6 V, and the high-current 3-state outputs can drive up to 15 LSTTL Loads. The devices have a low power consumption of 80-μA (Maximum) I_{CC}. Additionally, the devices have a low input current of 1 μA (Maximum) and a ±6-mA Output Drive at 5 V.

9.4 Device Functional Modes

Table 1 lists the functional modes of the SNx4HC595 devices.

Table 1. Function Table

INPUTS					FUNCTION
SER	SRCLK	$\overline{SRCLR}$	RCLK	$\overline{OE}$	
X	X	X	X	H	Outputs Q_A – Q_H are disabled.
X	X	X	X	L	Outputs Q_A – Q_H are enabled.
X	X	L	X	X	Shift register is cleared.
L	↑	H	X	X	First stage of the shift register goes low. Other stages store the data of previous stage, respectively.
H	↑	H	X	X	First stage of the shift register goes high. Other stages store the data of previous stage, respectively.
X	X	X	↑	X	Shift-register data is stored in the storage register.

10 Application and Implementation

10.1 Application Information

The SNx4HC595 is a low-drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs.

10.2 Typical Application

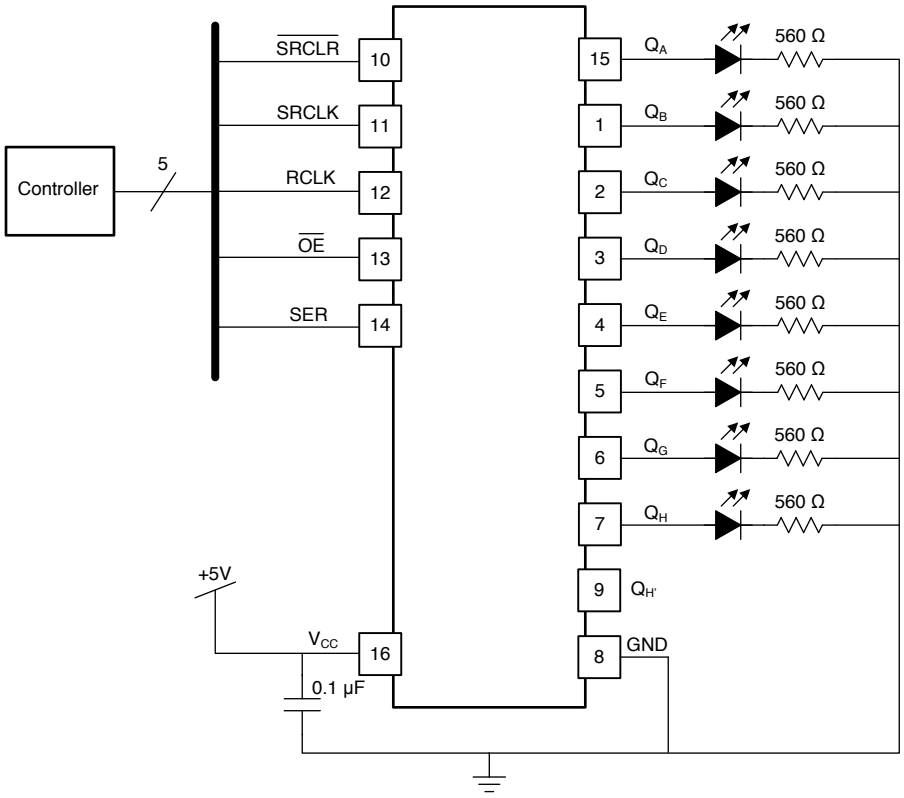


Figure 5. Typical Application Schematic

10.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

10.2.2 Detailed Design Procedure

- Recommended input conditions
  - Specified high and low levels. See (V_{IH} and V_{IL}) in the *Recommended Operating Conditions* table.
  - Specified high and low levels. See (V_{IH} and V_{IL}) in the *Recommended Operating Conditions* table.
  - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}
- Recommend output conditions
  - Load currents should not exceed 35 mA per output and 70 mA total for the part
  - Outputs should not be pulled above V_{CC}

Typical Application (continued)

10.2.3 Application Curves

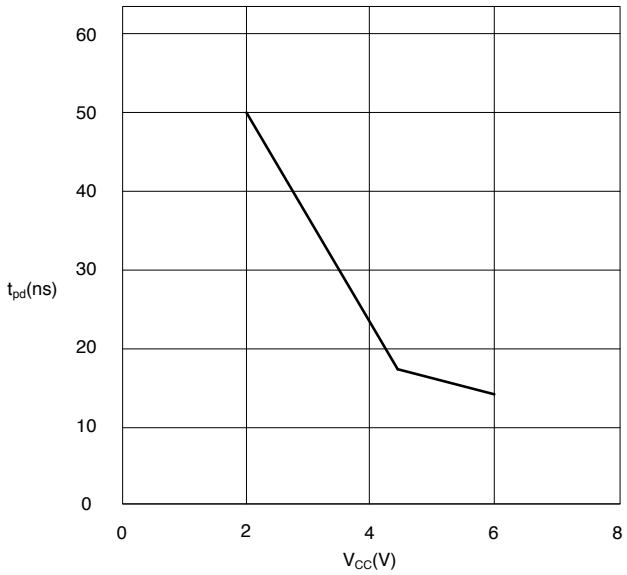


Figure 6. SN75HC595 t_{pd} vs. V_{CC}

11 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions* table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 µf is recommended; if there are multiple V_{CC} pins, then 0.01 µf or 0.022 µf is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 µf and a 1 µf are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

12 Layout

12.1 Layout Guidelines

When using multiple-bit logic devices, inputs should never float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Figure 7 specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the output section of the part when asserted. This will not disable the input section of the I/Os, so they cannot float when disabled.

12.2 Layout Example

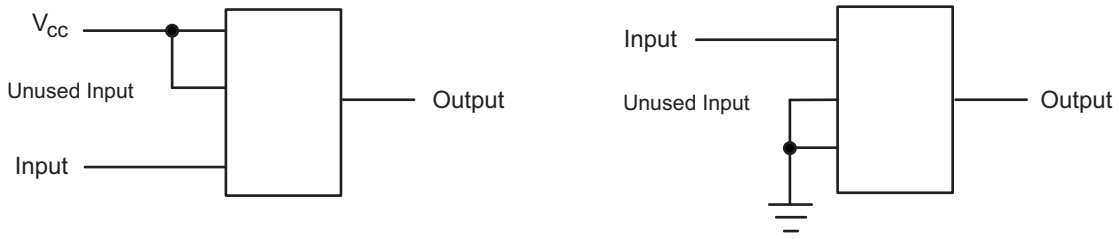


Figure 7. Layout Diagram